



PATENT
Attorney Docket No. ASC-022CPC1
(058420-157317)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Wu *et al.*
SERIAL NO.: 10/603,852 GROUP NO.: 2811
FILING DATE: June 25, 2003 EXAMINER: Douglas W. Owens
TITLE: ETCH STOP LAYER SYSTEM

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with 37 C.F.R. 1.98(a)(2), only copies of the foreign patent documents and non-patent publications are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

- ☐ (1) within three (3) months of the **filing date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or
- ☒ (2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and
- ☐ the requisite Statement is below, **OR**
- ☒ the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or

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- ☐ (3) after the mailing date of a **final action** or **notice of allowance** but before the payment of the **issue fee**, **AND**
- ☐ the requisite Statement is below, **AND**
- ☐ the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

STATEMENT

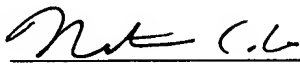
As required under 37 C.F.R. 1.97(e), Applicant(s), through the undersigned, hereby state either that:

- ☐ 1. Each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application **not more than three months** prior to the filing of the Information Disclosure Statement; or
- ☐ 2. No item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this Statement after making reasonable inquiry, no item of information contained in the Information Disclosure Statement was known to **any individual** designated in 37 C.F.R. 1.56(c) **more than three months** prior to the filing of the Information Disclosure Statement.

Respectfully submitted,

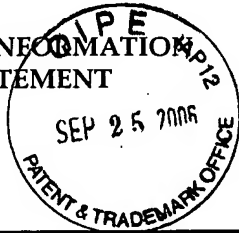
Date: September 21, 2006
Reg. No. 44,381

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FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-022CPC1

APPLICANTS: Wu *et al.*

SERIAL NO.: 10/603,852

FILING DATE: June 25, 2003 GROUP: 2811

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A268	2002/0190284	12/19/2002	Murthy et al.			
	A269	2002/0063292	05/30/2002	Armstrong			
	A270	2002/0167048	11/14/2002	Tweet et al.			
	A271	2004/0007715	01/15/2004	Webb et al.			
	A272	2004/007724	01/15/2004	Murthy et al.			
	A273	2004/0014276	01/22/2004	Murthy et al.			
	A274	2004/0084735	05/06/2004	Murthy et al.			
	A275	2004/0111901	06/24/2004	Schrom et al.			
	A276	4,969,031	11/00/1990	Kobayashi et al.			
	A277	5,013,681	05/07/1991	Kub et al.			
	A278	6,228,694	05/08/2001	Doyle et al.			
	A279	6,235,568	05/22/2001	Murthy et al.			
	A280	6,281,532	08/28/2001	Doyle et al.			
	A281	6,326,664	12/04/2001	Chau et al.			
	A282	6,489,639	12/30/2002	Hoke et al.			
	A283	6,563,152	05/13/2003	Roberds et al.			
	A284	6,591,321	07/08/2003	Aramilli et al.			
	A285	6,597,016	07/22/2003	Yuki et al.			
	A286	6,605,498	08/12/2003	Murthy et al.			
	A287	6,059,895	05/09/2000	Chu et al.			
	A288	6,621,131	09/16/2003	Murthy et al.			
	A289	6,657,223	12/02/2003	Wang et al.			
	A290	6,674,150	01/06/2004	Takagi et al.			
EXAMINER				DATE CONSIDERED			

FORM PTO - 1449					ATTORNEY DOCKET NO.: ASC-022CPC1				
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT					APPLICANTS: Wu <i>et al.</i>				
					SERIAL NO.: 10/603,852				
					FILING DATE: June 25, 2003 GROUP: 2811				
U.S. PATENT DOCUMENTS									
	A291	6,703,648	03/09/2004	Xiang					
	A292	6,743,684	06/01/2004	Liu					
	A293	6,790,747	09/14/2004	Henley et al.					
	A294	6,890,835	05/10/2005	Chu et al.					
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B55	0 828 296 A	03/11/1998	EP					
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C167	International Search Report and Written Opinion from the International Examining Authority for related application PCT/US01/19613, dated June 22, 2002							
	C168	Kuboto M., et al. "New SOI CMOS Process with Selective Oxidation, " IEEE IEDM TECH, DIG., pp. 814-816 (1986)							
	C169	Ming et al., "Interfacial roughness scaling and strain in lattice mismatched Si _{0.4} Ge _{0.6} thin films on Si" Applied Physics Letters, Vol. 67, No. 5, July 31, 1995, pp. 629-631							
	C170	Ming et al., "Microscopic structure of interfaces in Si _{1-x} Gex/Si heterostructures and superlattices studied by x-ray scattering and fluorescence yield, " Physical Review B, Vol. 47, No. 24, pp. 373-81, June 15, 1993							
	C171	Nishi et al. "Handbook of Semiconductor Manufacturing Technology," Marcel Dekker AG, New York, NY, 2000 pp. 1-22							
	C172	O'Neill, et al., "Deep Submicron CMOS Based on Silicon Germanium Technology," Fellow, IEEE Transactions on Electron Devices, Vol. 43, No. 6, June 1996 pp. 911-918							
EXAMINER					DATE CONSIDERED				

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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
	C173	Sugii, et al., "Role of Si1-xGex buffer layer on mobility enhancement in a strained-Si channel metal-oxide-semiconductor field-effect transistor," Central Research Laboratory, Hitachi Ltd. 1-280 Higashi-Koigakuboj, Kokubunji-shi, Tokyo 185-8601 Japan, pp. 2948-2950	
	C174	Vossen et al. "Thin Film Processes II" Academic Press Inc., San Diego, CA 1991, pp. 370-442	
	C175	Wolfe et al. "Silicon Processing for the VLSI ERA, Volume 1; Process Technology," Marcel Dekker AG, New York, NY, 2000, pp. 1-22	
EXAMINER		DATE CONSIDERED	

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